

## P-Channel Enhancement Mode MOSFET

### 1. Product Information

#### 1.1 Features

- ✓ Surface-mounted package
- ✓ Super Trench
- ✓ Advanced trench cell design

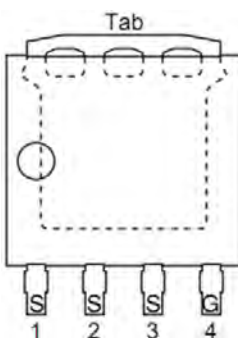
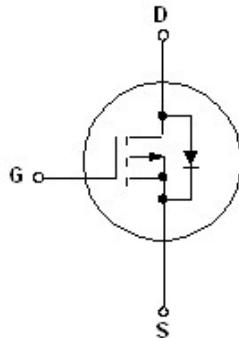
#### 1.2 Applications

- ✓ BMS
- ✓ Drones
- ✓ High power inverter system
- ✓ Light electric vehicles

#### 1.3 Quick reference

- ✓  $BV \geq -60\text{ V}$
- ✓  $P_{tot} \leq 107\text{ W}$
- ✓  $I_D \leq -40\text{ A}$
- ✓  $R_{DS(ON)} \leq 28\text{ m}\Omega @ V_{GS} = -10\text{ V}$
- ✓  $R_{DS(ON)} \leq 40\text{ m}\Omega @ V_{GS} = -4.5\text{ V}$

### 2. Pin Description

| Pin   | Description | Simplified Outline                                                                                                | Symbol                                                                                |
|-------|-------------|-------------------------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------|
| 1,2,3 | Source      |  <p>Top View<br/>LFPAK5*6</p> |  |
| 4     | Gate        |                                                                                                                   |                                                                                       |
| Tap   | Drain       |                                                                                                                   |                                                                                       |

## 3. Limiting Values

| Symbol                  | Parameter                               | Rating                              | Unit                          |
|-------------------------|-----------------------------------------|-------------------------------------|-------------------------------|
| $V_{DS}$                | Drain-Source Voltage                    | -60                                 | V                             |
| $V_{GS}$                | Gate-Source Voltage                     | $\pm 20$                            | V                             |
| $I_D$                   | Drain Current                           | $T_C = 25\text{ }^{\circ}\text{C}$  | A                             |
|                         |                                         | $T_C = 100\text{ }^{\circ}\text{C}$ | A                             |
| $I_{DM}^{Note2}$        | Pulsed Source Current                   | $T_C = 25\text{ }^{\circ}\text{C}$  | A                             |
| $I_S$                   | Diode Forward Current                   | $T_C = 25\text{ }^{\circ}\text{C}$  | A                             |
| $E_{AS}$                | Single Pulsed Avalanche Energy          | $L = 1.0\text{mH}$                  | mJ                            |
| $P_{tot}$               | Total Power Dissipation                 | $T_C = 25\text{ }^{\circ}\text{C}$  | W                             |
| $R_{\theta JA}^{Note1}$ | Thermal Resistance- Junction to Ambient | 62                                  | $^{\circ}\text{C} / \text{W}$ |
| $R_{\theta JC}$         | Thermal Resistance- Junction to Case    | 1.4                                 | $^{\circ}\text{C} / \text{W}$ |
| $T_{stg}$               | Storage Temperature                     | -55~175                             | $^{\circ}\text{C}$            |
| $T_J$                   | Junction Temperature                    | 175                                 | $^{\circ}\text{C}$            |

Note 1 : Surface Mounted on 1 in<sup>2</sup> pad area,  $t \leq 10$  sec.

Note 2 : Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

Note 3 : Limited by bonding wire.

## 4. Marking Information

| Product Name | Marking                                                                 |
|--------------|-------------------------------------------------------------------------|
| UK250P06LF   | <div>250P06<br/>YWW01<br/>AAAAAA</div> <div>YWWXXX:<br/>Date Code</div> |

## 5. Ordering Code

| Product Name | Package | Reel Size | Tape width | Quantity | Note |
|--------------|---------|-----------|------------|----------|------|
| UK250P06LF   | LFPK5*6 |           |            | 5000     |      |

## 6. Electrical Characteristics ( $T_A=25^\circ$ Unless Otherwise Noted )

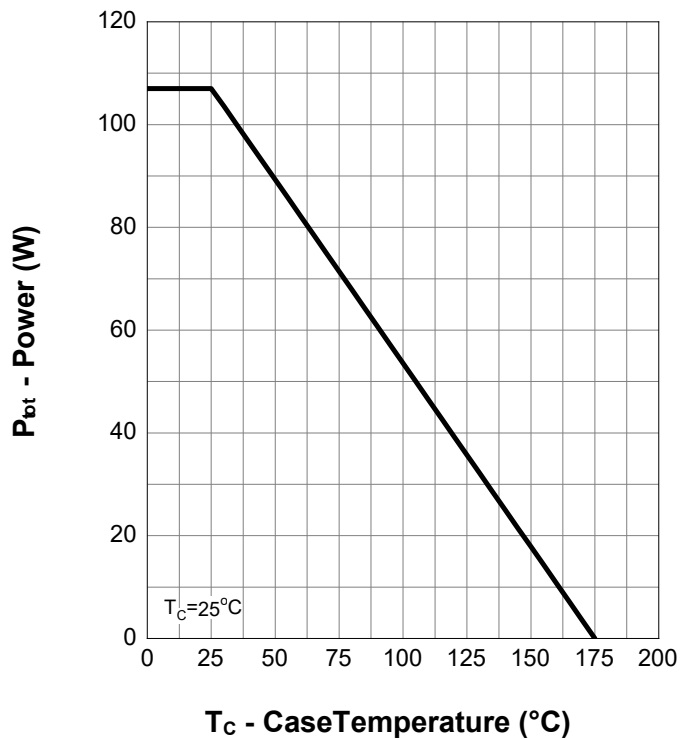
| Symbol                                       | Parameter                      | Conditions                                                                                                                   | Min | Typ  | Max  | Unit |
|----------------------------------------------|--------------------------------|------------------------------------------------------------------------------------------------------------------------------|-----|------|------|------|
| Static Characteristics                       |                                |                                                                                                                              |     |      |      |      |
| BV <sub>DSS</sub>                            | Drain-Source Breakdown Voltage | V <sub>GS</sub> = 0 V, I <sub>DS</sub> = -250 μA                                                                             | -60 | -    | -    | V    |
| V <sub>GS(th)</sub>                          | Gate Threshold Voltage         | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>DS</sub> = -250 μA                                                                | -1  | -    | -2   | V    |
| I <sub>DSS</sub>                             | Drain Leakage Current          | V <sub>DS</sub> = -48V, V <sub>GS</sub> = 0 V                                                                                | -   | -    | -1   | μA   |
| I <sub>GSS</sub>                             | Gate Leakage Current           | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 20 V                                                                              | -   | -    | ±100 | nA   |
| R <sub>DS(ON)</sub> <sup>Note1</sup>         | On-State Resistance            | V <sub>GS</sub> = -10 V, I <sub>DS</sub> = -10 A                                                                             | -   | 25   | 28   | mΩ   |
|                                              |                                | V <sub>GS</sub> = -4.5V, I <sub>DS</sub> = -5A                                                                               | -   | 35   | 40   |      |
| Diode Characteristics                        |                                |                                                                                                                              |     |      |      |      |
| V <sub>SD</sub> <sup>Note1</sup>             | Diode Forward Voltage          | I <sub>SD</sub> = -10 A, V <sub>GS</sub> = 0 V                                                                               | -   | -    | -1.3 | V    |
| t <sub>rr</sub>                              | Reverse Recovery Time          | I <sub>DS</sub> = -10 A, V <sub>GS</sub> = 0 V<br>dI <sub>SD</sub> /dt = 100 A/μs                                            | -   | 19   | -    | nS   |
| Q <sub>rr</sub>                              | Reverse Recovery Charge        |                                                                                                                              | -   | 16   | -    | nC   |
| Dynamic Characteristics <sup>Note2</sup>     |                                |                                                                                                                              |     |      |      |      |
| C <sub>iss</sub>                             | Input Capacitance              | V <sub>GS</sub> = 0 V, V <sub>DS</sub> = -30 V<br>Frequency = 1 MHz                                                          | -   | 2240 | -    | pF   |
| C <sub>oss</sub>                             | Output Capacitance             |                                                                                                                              | -   | 113  | -    |      |
| C <sub>rss</sub>                             | Reverse Transfer Capacitance   |                                                                                                                              | -   | 85   | -    |      |
| t <sub>d(on)</sub>                           | Turn-on Delay Time             | V <sub>DS</sub> = -30 V, V <sub>GEN</sub> = -10 V,<br>R <sub>G</sub> = 3.9 Ω, R <sub>L</sub> =3Ω,<br>I <sub>DS</sub> = -10 A | -   | 7    | -    | nS   |
| t <sub>r</sub>                               | Turn-on Rise Time              |                                                                                                                              | -   | 15   | -    |      |
| t <sub>d(off)</sub>                          | Turn-off Delay Time            |                                                                                                                              | -   | 63   | -    |      |
| t <sub>f</sub>                               | Turn-off Fall Time             |                                                                                                                              | -   | 26   | -    |      |
| Gate Charge Characteristics <sup>Note2</sup> |                                |                                                                                                                              |     |      |      |      |
| Q <sub>g</sub>                               | Total Gate Charge              | V <sub>DS</sub> = -30 V, V <sub>GS</sub> = -10 V,<br>I <sub>DS</sub> = -10A                                                  | -   | 47   | -    | nC   |
| Q <sub>gs</sub>                              | Gate-Source Charge             |                                                                                                                              | -   | 11   | -    |      |
| Q <sub>gd</sub>                              | Gate-Drain Charge              |                                                                                                                              | -   | 6    | -    |      |

Note 1: Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

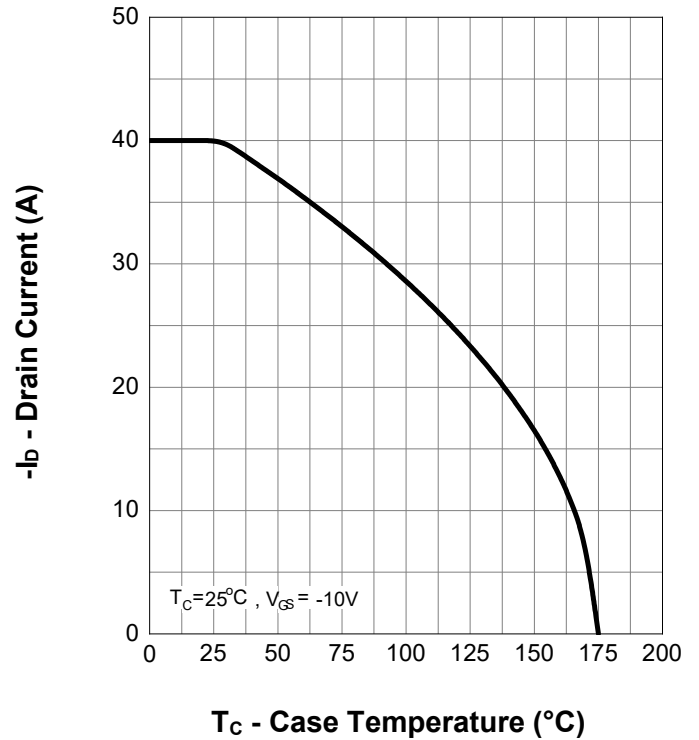
Note 2: Guaranteed by design, not subject to production testing.

## 7. Typical Characteristics

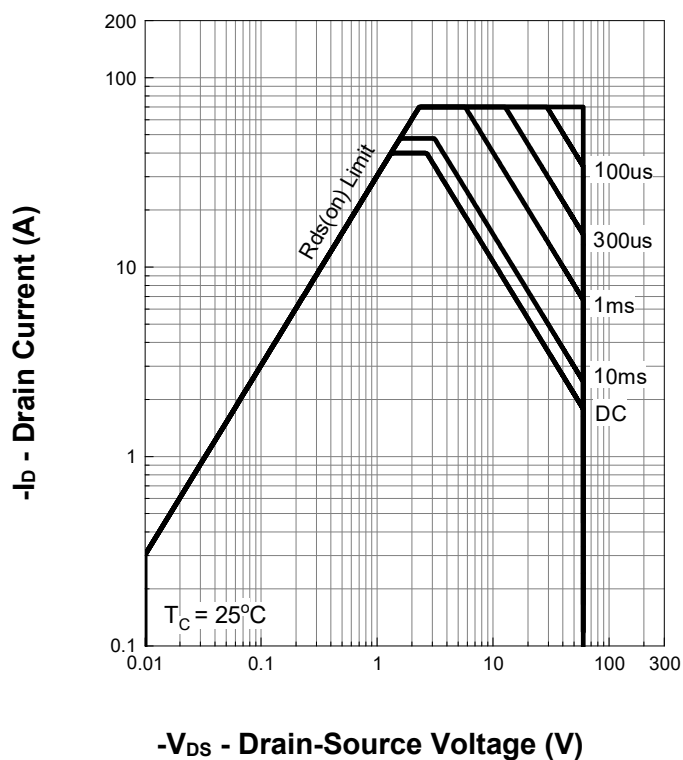
Power Capability



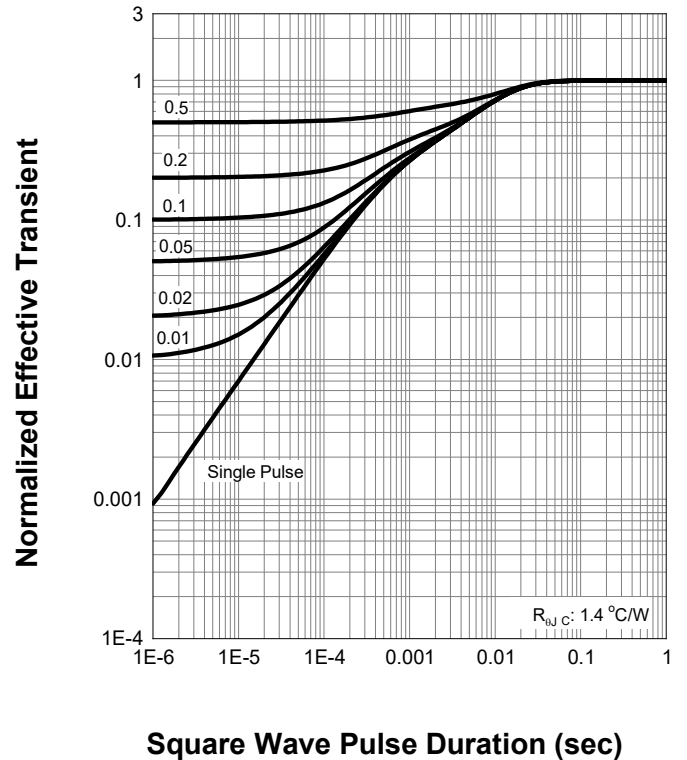
Current Capability



Safe Operating Area

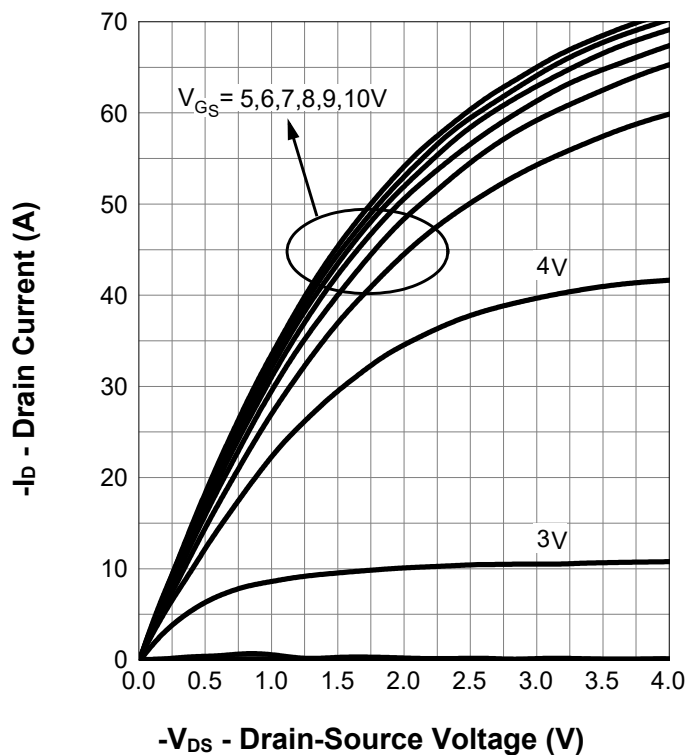


Transient Thermal Impedance

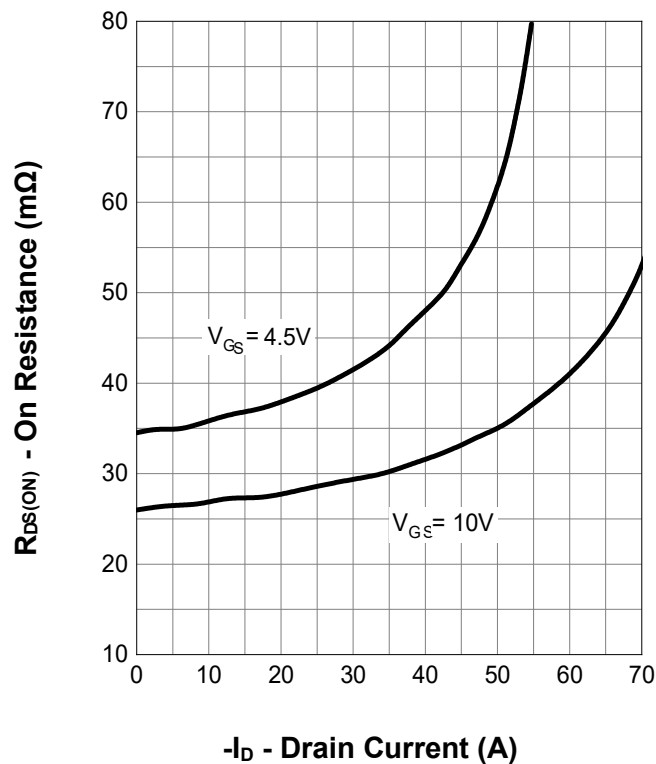


## 7. Typical Characteristics (cont.)

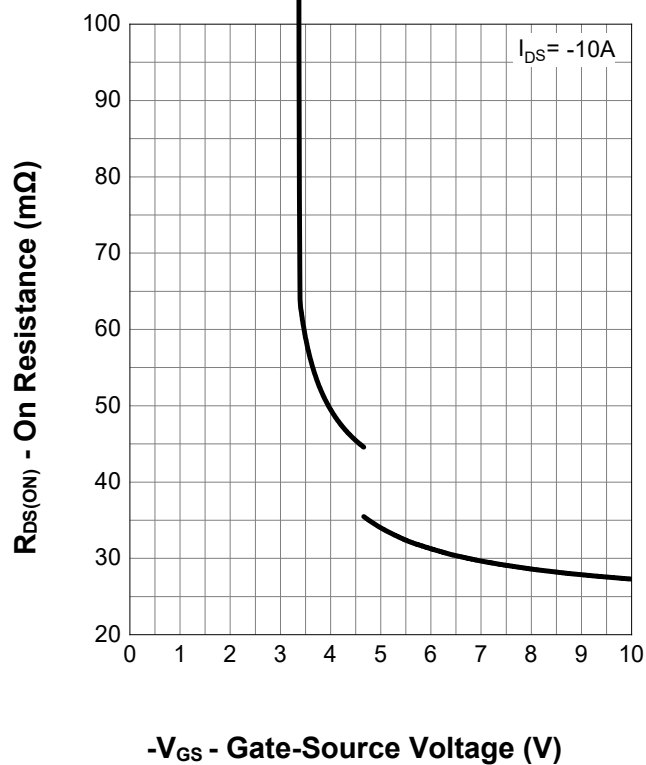
Output Characteristics



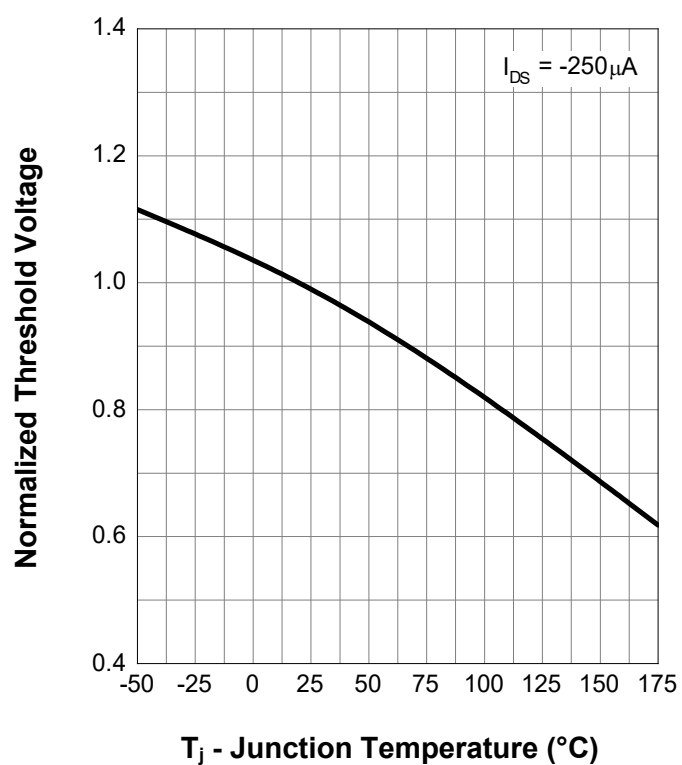
On Resistance



Transfer Characteristics

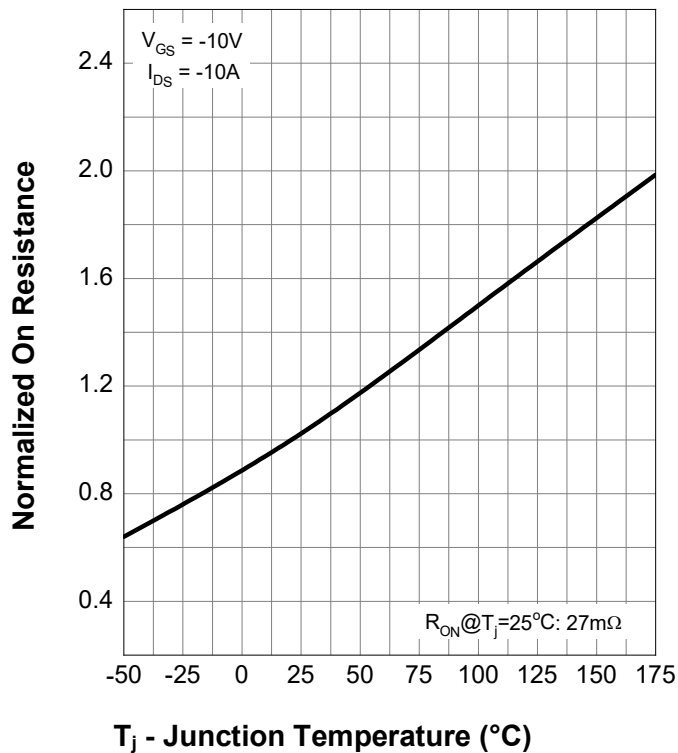


Normalized Threshold Voltage

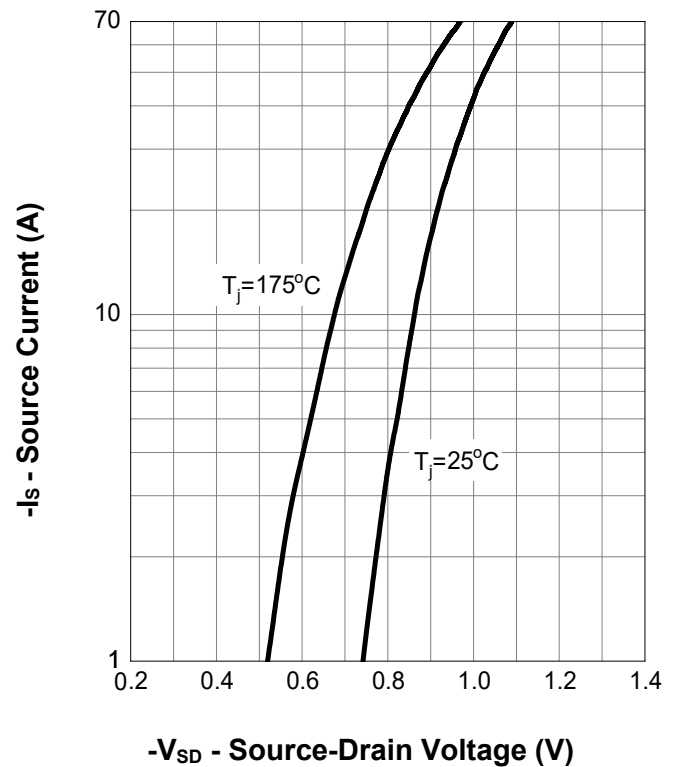


## 7. Typical Characteristics (cont.)

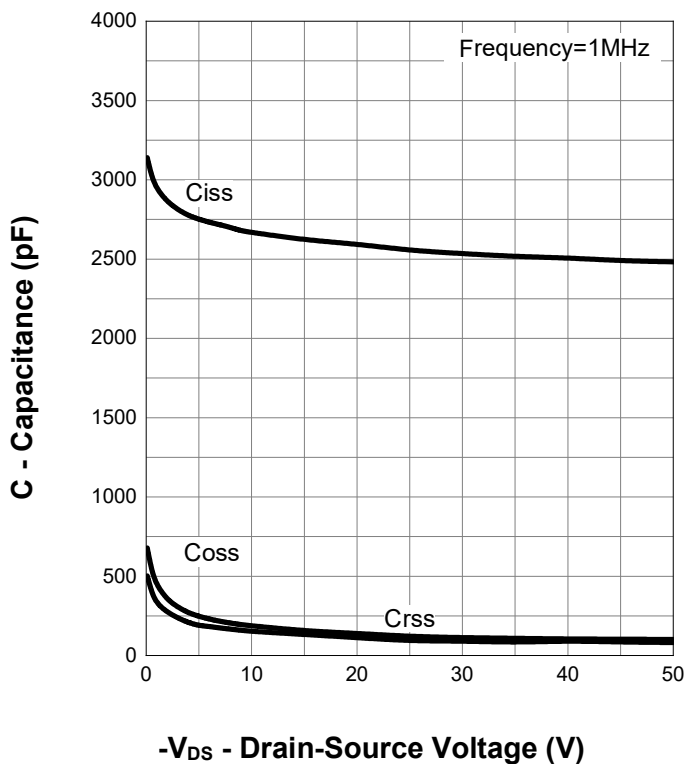
Normalized On Resistance



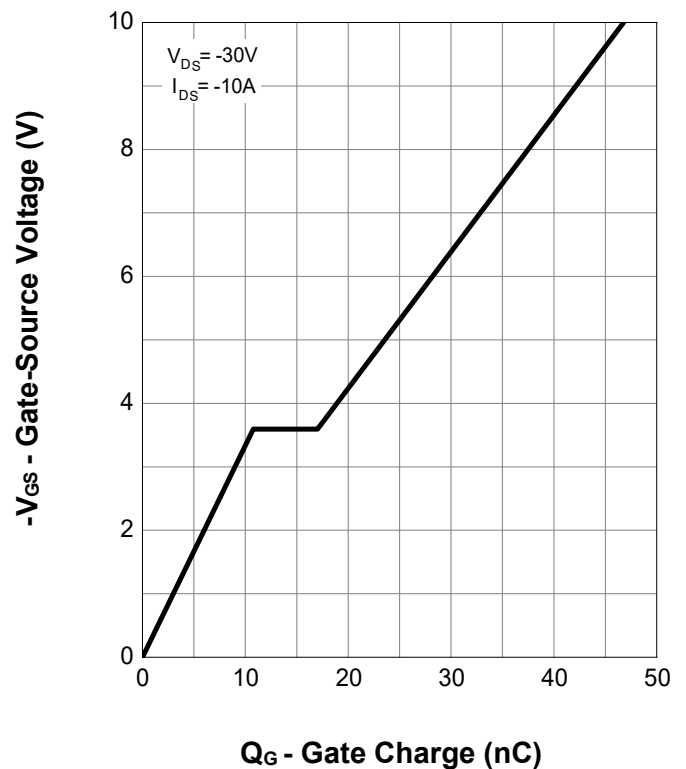
Diode Forward Current



Capacitance

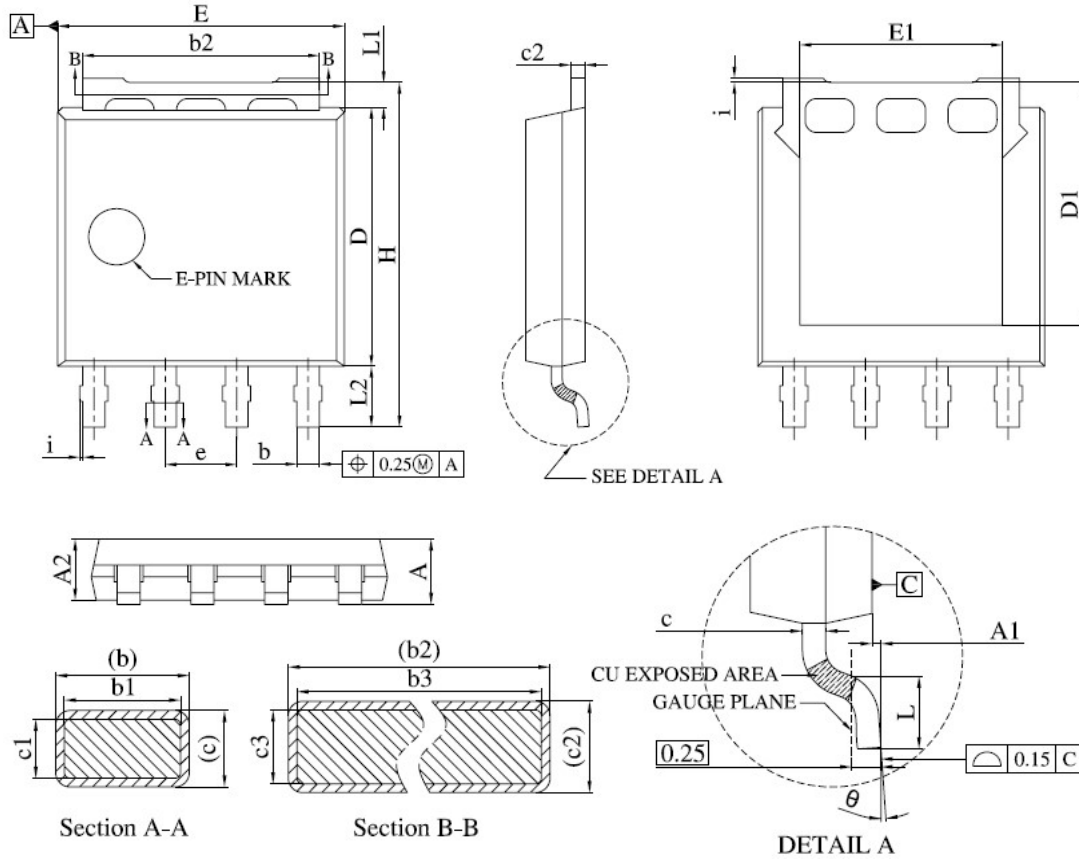


Gate Charge



## 8. Package Dimensions

### LFPK5\*6 Package



| Symbol | Dimensions In Millimeters |      |
|--------|---------------------------|------|
|        | MIN.                      | MAX. |
| A      | 1.00                      | 1.30 |
| A1     | 0.00                      | 0.15 |
| A2     | 0.98                      | 1.12 |
| b      | 0.35                      | 0.50 |
| b1     | 0.32                      | 0.46 |
| b2     | 4.02                      | 4.41 |
| b3     | 4.00                      | 4.37 |
| c      | 0.19                      | 0.25 |
| c1     | 0.17                      | 0.23 |
| c2     | 0.24                      | 0.30 |
| c3     | 0.22                      | 0.28 |
| D      | 4.45                      | 4.70 |
| D1     | -                         | 4.45 |
| E      | 4.95                      | 5.30 |
| E1     | 3.50                      | 3.70 |
| e      | 1.27 BSC.                 |      |

| Symbol   | Dimensions In Millimeters |      |
|----------|---------------------------|------|
|          | MIN.                      | MAX. |
| H        | 5.95                      | 6.25 |
| i        | -                         | 0.25 |
| L        | 0.40                      | 0.85 |
| L1       | 0.27                      | 0.57 |
| L2       | 0.80                      | 1.30 |
| $\theta$ | 0°                        | 8°   |